

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Divisional Application of U.S. 09/102,665

Hideki MATSUMURA et al.

Serial No.: NEW

Group Art Unit: 1763 (Expected)

Filed: January 10, 2002

Examiner: Lund, J. (Expected)

For: METHOD AND APPARATUS FOR DEPOSITING A THIN FILM,
AND SEMICONDUCTOR DEVICE HAVING A SEMICONDUCTOR-
INSULATOR JUNCTION

PRELIMINARY AMENDMENT

Commissioner of Patents
Washington, D.C. 20231

Date: January 10, 2002

Sir:

This is a Preliminary Amendment for the above-captioned Divisional application, concurrently filed herewith. Please amend the above-captioned Divisional application as follows:

IN THE CLAIMS:

Please **CANCEL** claims 1-17 without prejudice or disclaimer and **ADD** the following new claim 19:

19. (NEW) Semiconductor device as claimed in claim 18, wherein said semiconductor-insulation junction is one obtained by deposition of said insulator film, which is carried out in said same process chamber after said treatment and utilizes a reaction of a deposition gas supplied with said substrate via said same thermal catalysis body.

REMARKS

Claims 1 to 17 have been canceled and claim 19 has been added to particularly point out and distinctly claim the subject matter which the applicants regard as their invention.

The above amendment is believed to place the claims in proper condition for examination.

Early and favorable action is awaited.

In the event that any fees are due in connection with this paper, please charge our Deposit Account No. 01-2340.

Respectfully submitted,

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Enclosure: Version with Markings Showing Changes Made

VERSION WITH MARKING TO SHOW CHANGING MADE

IN THE CLAIMS

Please ADD the claim 19 as follows:

19. (NEW) Semiconductor device as claimed in claim 18, wherein said semiconductor-insulation junction is one obtained by deposition of said insulator film, which is carried out in said same process chamber after said treatment and utilizes a reaction of a deposition gas supplied with said substrate via said same thermal catalysis body.